

. reescale Semiconductor Technical Data

Replaced by MHW9276N. There are no form, fit or function changes with this part replacement. N suffix indicates RoHS compliant part.

Gallium Arsenide CATV Amplifier Module

Features

- 79-, 112- and 132-Channel Loading
- Excellent Distortion Performance
- Integrated ESD Protection Diodes
- GaAs FET Transistor Technology
- Unconditionally Stable Under All Load Conditions

Applications

- CATV Systems Operating in the 40 to 870 MHz Frequency Range
- Input Stage Amplifier in Optical Nodes, Line Extenders and Trunk Distribution Amplifiers for CATV Systems
- Driver Amplifier in Linear General Purpose Applications

Description

24 Vdc Supply, 40 to 870 MHz, CATV GaAs Forward Amplifier Module

Document Number: MHW9276

Rev. 3, 5/2006

MHW9276

870 MHz **27.9 dB GAIN** 132-CHANNEL **GaAs CATV AMPLIFIER MODULE**

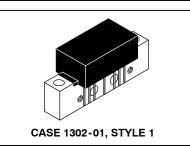


Table 1. Maximum Ratings

Rating	Symbol	Value	Unit
RF Voltage Input (Single Tone)	V _{in}	+65	dBmV
DC Supply Voltage	V _{CC}	+26	Vdc
Operating Case Temperature Range	T _C	-20 to +100	°C
Storage Temperature Range	T _{stg}	-40 to +100	°C

Table 2. ESD Maximum Ratings

Rating	Input Value	Output Value	Unit
Surge Voltage per IEC 1000-4-5	200	200	V
Human Body Model per Mil. Std. 1686	2	2	kV

Table 3. Electrical Characteristics ($V_{CC} = 24 \text{ Vdc}$, $T_C = +30^{\circ}\text{C}$, 75 Ω system unless otherwise noted)

Characteristic		Symbol	Min	Тур	Max	Unit
Frequency Range		BW	40	_	870	MHz
Power Gain	870 MHz	G _p	27	27.9	28.5	dB
Slope	40-870 MHz	S	0.4	0.95	1.4	dB
Gain Flatness (40-870 MHz, Peak	-to-Valley)	G _F	_	_	0.8	dB



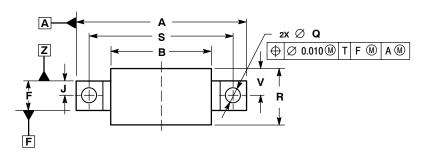
Table 3. Electrical Characteristics (V_{CC} = 24 Vdc, T_{C} = +30°C, 75 Ω system unless otherwise noted) (continued)

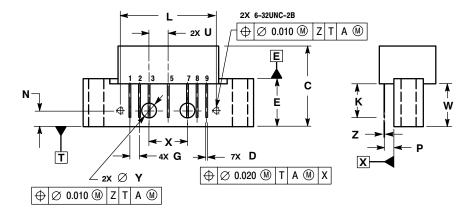
Characteristic		Symbol	Min	Тур	Max	Unit
Input Return Loss (Z ₀ = 75 Ohms)	40-200 MHz 201-600 MHz 601-870 MHz	IRL	20 19 18			dB
Output Return Loss (Z ₀ = 75 Ohms)	40-200 MHz 201-600 MHz 601-870 MHz	ORL	20 18 18			dB
Composite Second Order (V _{out} = +44 dBmV/ch., Worst Case) (V _{out} = +44 dBmV/ch., Worst Case) (V _{out} = +44 dBmV/ch., Worst Case)	79-Channel FLAT 112-Channel FLAT 132-Channel FLAT	CSO ₇₉ CSO ₁₁₂ CSO ₁₃₂	_ _ _	-70 -66 -66	-64 -62 -60	dBc
Cross Modulation Distortion @ Ch 2 (V _{out} = +44 dBmV/ch., FM = 55.25 MHz) (V _{out} = +44 dBmV/ch., FM = 55.25 MHz) (V _{out} = +44 dBmV/ch., FM = 55.25 MHz)	79-Channel FLAT 112-Channel FLAT 132-Channel FLAT	$\begin{array}{c} {\sf XMD_{79}} \\ {\sf XMD_{112}} \\ {\sf XMD_{132}} \end{array}$	_ _ _	-60 -60 -60	-53 -53 -53	dBc
Composite Triple Beat (V _{out} = +44 dBmV/ch., Worst Case) (V _{out} = +44 dBmV/ch., Worst Case) (V _{out} = +44 dBmV/ch., Worst Case)	79-Channel FLAT 112-Channel FLAT 132-Channel FLAT	CTB ₇₉ CTB ₁₁₂ CTB ₁₃₂	_ _ _	-71 -68 -66	-65 -61 -60	dBc
Noise Figure	50 MHz 550 MHz 750 MHz 870 MHz	NF	 	5.0 5.0 5.0 5.0	5.5 — — 6.5	dB
DC Current (V _{DC} = 24 V, T _C = 45°C)		I _{DC}	235	250	265	mA



ARCHIVE INFORMATION

PACKAGE DIMENSIONS





- NOTES:
 1. DIMENSIONS ARE IN INCHES.
 2. INTERPRET DIMENSIONS AND INTERPRET DIMENSIONS AND TOLERANCES PER ASME Y14.5M, 1994.

	INCHES		MILLIN	MILLIMETERS		
DIM	MIN	MAX	MIN	MAX		
Α		1.775		45.085		
В		1.085		27.559		
С		0.840		21.336		
D	0.015	0.021	0.381	0.533		
E	0.465	0.510	11.811	12.954		
F	0.300	0.325	7.62	8.255		
G	0.100 BSC 0.156 BSC		2.540 BSC			
J			3.962 BSC			
K	0.315	0.355	8.001	9.017		
L	1.000 BSC		25.400 BSC			
N	0.165 BSC		4.191 BSC			
P	0.100 BSC		2.540 BSC			
Q	0.148	0.168	3.759	4.267		
R		0.600		15.24		
S	1.500 BSC 0.200 BSC		38.100 BSC			
U			5.080 BSC			
٧		0.250		6.350		
W	0.435		11.049			
Х	0.400 BSC		10.160 BSC			
Υ	0.152	0.163	3.861	4.140		
Z	0.009	0.011	0.229	0.279		

- STYLE 1:
 PIN 1. RF INPUT
 2. GROUND
 3. GROUND
 4. DELETED
 5. VDC
 6. DELETED
 7. GROUND
 8. GROUND
 9. RF OUTPUT

CASE 1302-01 ISSUE B





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